TO-126F	PNP	Silicon PNP transistor in a TO-126F Plastic Package.

/ Absolute Maximum Ratings(Ta=25)

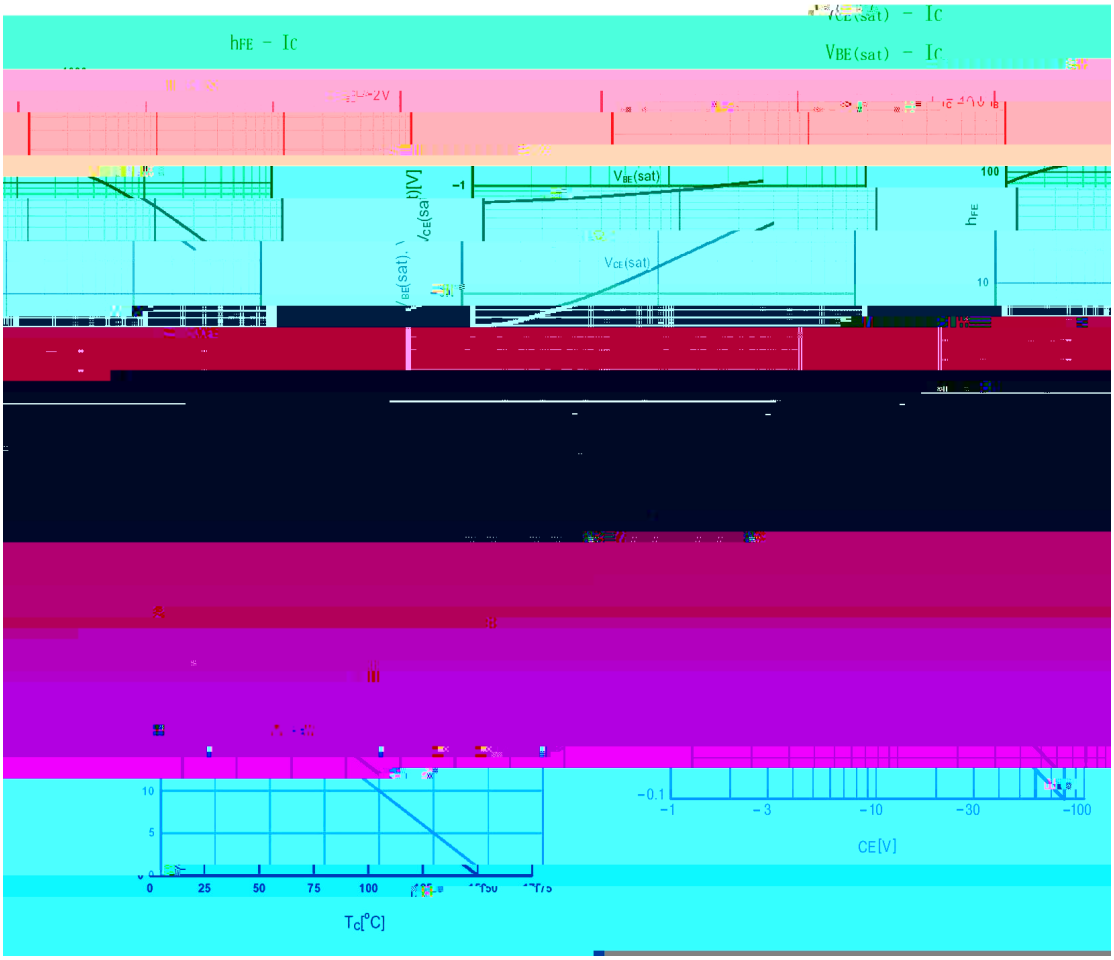
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Collector Current – Continuous	I_{CM}	-6.0	A
Collector Power Dissipation	P_C(Tc=25)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

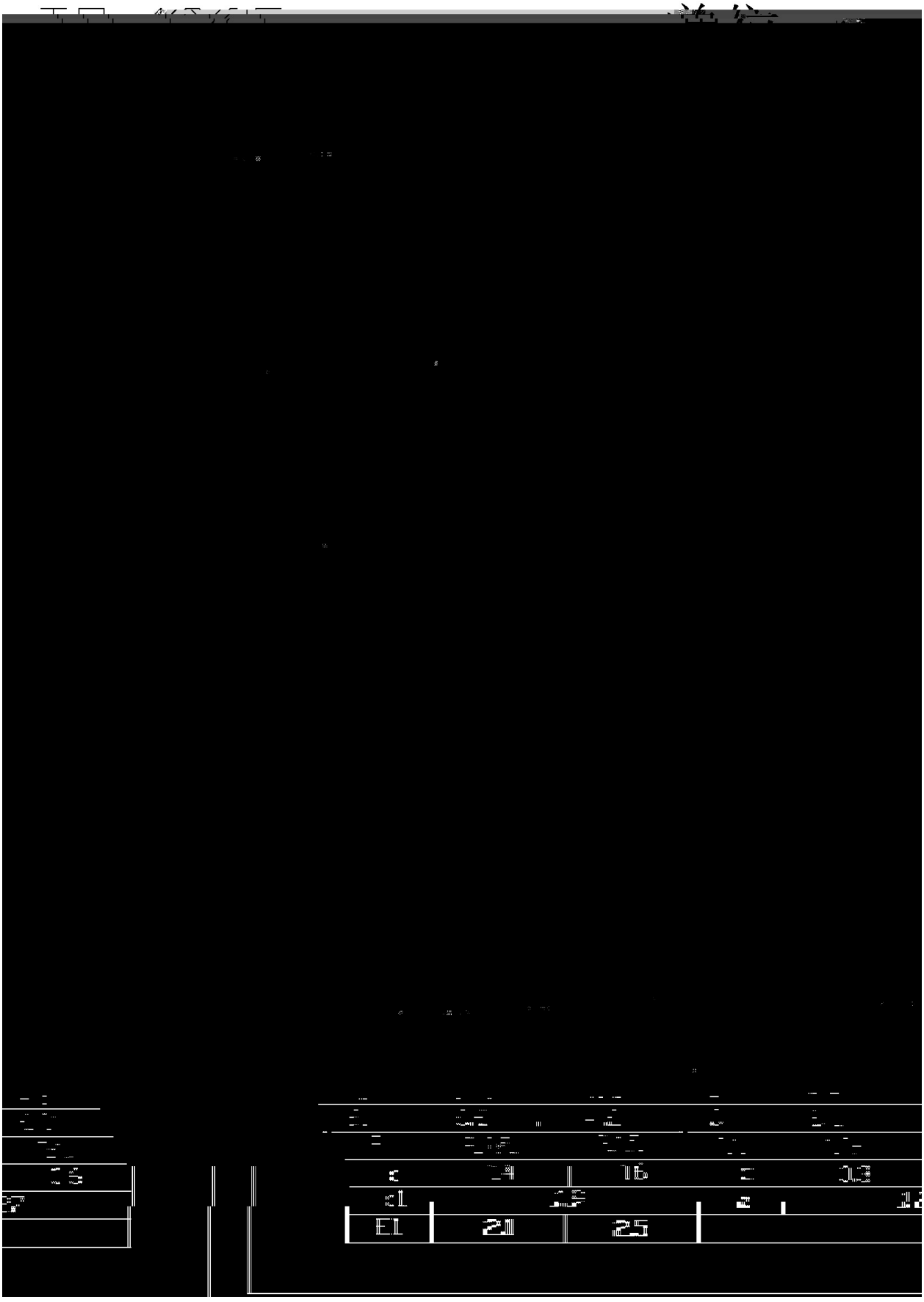
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	*V_{CEO}	I_C=-100mA I_B=0	-80			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-80V I_E=0			-0.1	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-1.0	mA
DC Current Gain	*$h_{FE(1)}$	V_{CE}=-2.0V I_C=-150mA	40			
	*$h_{FE(2)}$	V_{CE}=-2.0V I_C=-1.0A	25			
Collector to Emitter Saturation Voltage	*$V_{CE(sat)}$	I_C=-1.0A I_B=-0.1A			-0.6	V
Base to Emitter Voltage	*V_{BE}	V_{CE}=-2.0V I_C=-1.0A			-1.3	V
Transition Frequency	f_T	V_{CE}=-10V I_C=-250mA	3.0			MHz

* Pulse test: pulse width =300μs;duty cycle 1.5%. =300μs 1.5%

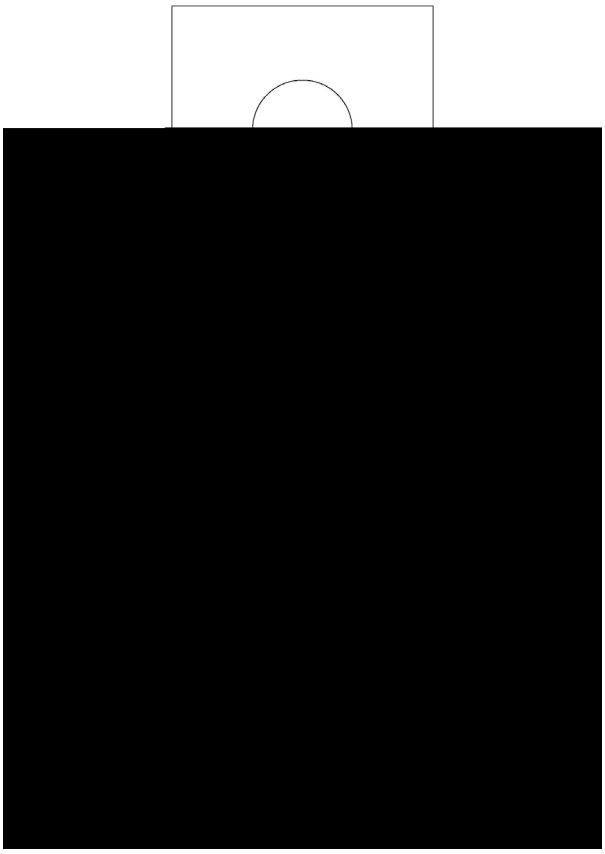
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

BD238

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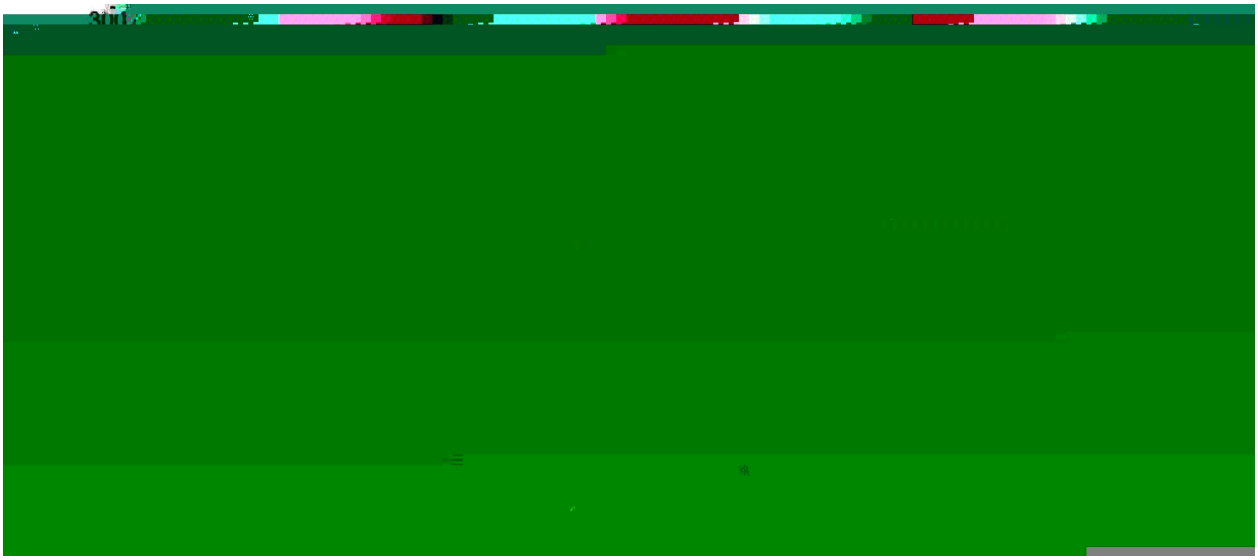
Note:

BR:	Company Code
BD238:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



						Note:	
1		25	150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.	
2		255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3				2 10 /sec.		3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm^3)